

Electronic Acknowledgement Receipt

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International Application Number:	
Confirmation Number:	2319
Title of Invention:	Stacked structure and production method thereof
First Named Inventor/Applicant Name:	Hubert Moriceau
Customer Number:	90678
Filer:	Jasper W. Dockrey/Christine Pisarski
Filer Authorized By:	Jasper W. Dockrey
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Application Type:	U.S. National Stage under 35 USC 371

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File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/Message Digest	Multi Part/.zip	Pages (if appl.)
1	Foreign Reference	RU-1282757.pdf	215504 9db986ef97e957e00ba441d4f13fa05875f1 70fc	no	7

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2	Foreign Reference	WO-9520824A1.pdf	852361 39dfb9e8f417133bf0cb416458df6ca070c2 60f7	no	24
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3	Foreign Reference	WO-9908316.pdf	724323 83c0f0c01812a8264710dd5150b3cea234a ef6d5	no	22
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4	Foreign Reference	WO-9935674A1.pdf	1786999 44577315fa0d80da096bc981ce43cefa78e9 d98a	no	44
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5	Foreign Reference	WO-9939378.pdf	1169894 2b426d9a3969d10aea77b6af30c794d4eea 48717	no	31
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6	Foreign Reference	WO-0048238A1.pdf	2047387 9d232deca54a514863d796e3504b4f993e b6d81	no	55
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7	Foreign Reference	WO-0063965A1.pdf	3396107 8b191326ec76ca98e8d087a0b4a814d1872 f47c2	no	78
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9	Foreign Reference	WO-0143168A2.pdf	1163934 8335dc78f8c956ad3486ccbf42879db94d 25290	no	31
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10	Foreign Reference	WO-0205344A1.PDF	1241265 086b2ed8c34999c8d2a6d4046386bc10b3 7bf83	no	30
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12	Foreign Reference	WO-02083387A1.pdf	1908535 c60bb7ad332d005424b0ae77d9b6f876ba7 474e4	no	46
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13	Foreign Reference	WO-03013815A1.pdf	3138850 9665631b2a854dc42bd8323794fcfd6f2911 dccdc	no	70
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14	NPL Documents	Agarwal-Aditya-Efficient-Production-of-Silicon.pdf	332510 b89d7292e9e7bc88659a63b128d7e90385 4fd888	no	2
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15	NPL Documents	Ahn-K-YI-Growth-Shrinkage.pdf	905943 fe1b18abe1a77308759d541f91305988c73 0b5c2	no	11
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16	NPL Documents	Almeida-et-al-Bond-Formation-In-ION-Beam.pdf	233126 b334963be1ca36e7df32bae26bc1cf9856 def3	no	5
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17	NPL Documents	Ascheron-C-et-al-A-Comparative-Study.pdf	805187 aa5b6d0b99d846f0f707979860c2a87d15a 56f53	no	10
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25	NPL Documents	Aspar_et_al_Smart_Cut_The_basic_fabrication_process_UNIBOND.pdf	462907 411623f274decd4324b4bd1c62f7f42f5c9 e43b	no	10
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29	NPL Documents	Aspar_B_et_al_Transfer_of_Structured_and_Patterned_Thin.pdf	80682 4807811e307cd1c1dc19c0c31964e83c40b 54e9f	no	2
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35	NPL Documents	Blochl_P_et_al_Frist-Principles_Calculations_of_Diffusion_Coefficients.pdf	290290 4a7bf7851fdc2e5036bb42945bbd513b3a4 7a80d	no	4
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37	NPL Documents	Bruel_M_et_al_Vol_99-1_Meeting_Abstract.pdf	127811 37ed322e0f2852c05a24cb4c307e3d844cd 4e956	no	2
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38	NPL Documents	Bruel_Michel_Application_of_Hydrogen_on_Beams_to_Silicon.pdf	483916 dd5290d8cc824ccc32f867cd44748958e663db3d	no	7
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39	NPL Documents	Bruel_M_et_al_Smart_Cut_A_New_Silicon_on_Insulator_Material.pdf	374214 a42c89798c1c4a78ade3c5c4b5dc5714379a721f	no	6
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45	NPL Documents	Camperi-Ginestet_et_al_Alignable_Epitaxial_Liftoff.pdf	312927 fd8761331bd75d5fb848e66373d1ac2752c37aa7	no	4
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47	NPL Documents	Carter-et-al-Applications-of-Ion-Beams-To-Materials.PDF	600857 2313c4539fcc7c3808380d3dfcbdb24b7d2abfc2	no	13
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48	NPL Documents	Carter_G_et_al_The_Collection_of_Ions_Implanted_in_Semiconductors_ll.pdf	669972 318947fb496c9a661b960b5823aafa38615b5408	no	8
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53	NPL Documents	Chu_WK_et_al_Radiation_Damage_of_50-250_keV_Hydrogen.pdf	663443 5f5f7f6c209a80cd60eb9bea796910ad3d19a15	no	10
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54	NPL Documents	Chu_Ion_Implantation_In_Semiconductors.PDF	499300 9988f6882ac689449d57f10540047e8f65595bec	no	12
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Total Files Size (in bytes):				45684769	
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